

< HVMOSFET MODULE >

FMF200DC-66BE

HIGH POWER SWITCHING USE

INSULATED TYPE

2nd gen. HVMOSFET (High Voltage Metal Oxide Semiconductor Field Effect Transistor) Modules

FMF200DC-66BE



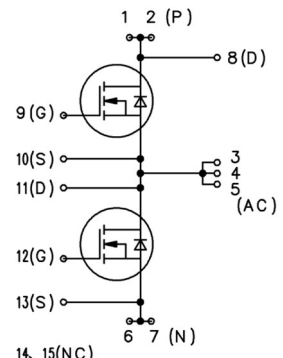
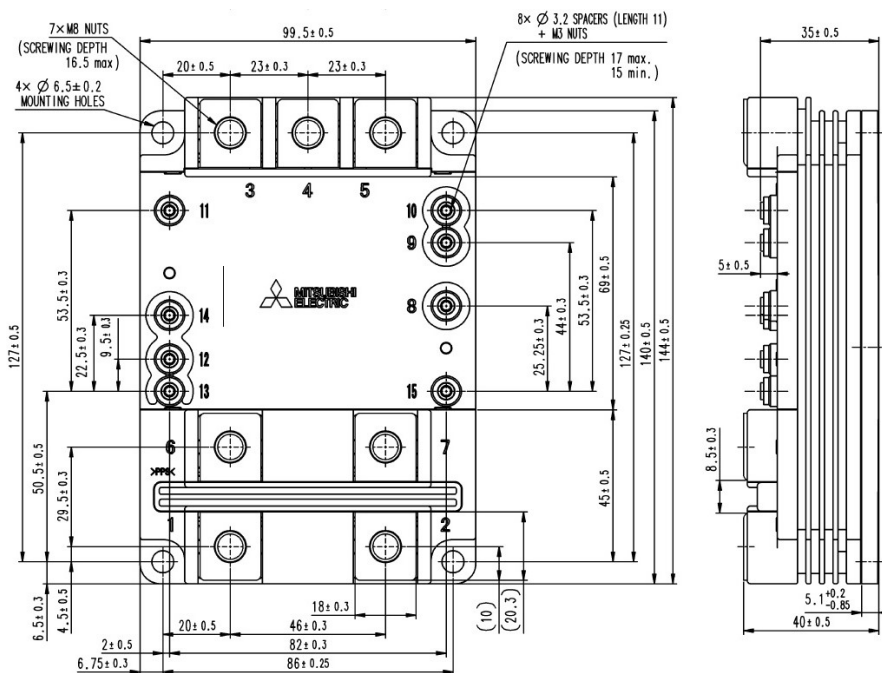
- I_D200A
- V_{DSX}3300V
- 2-element in a Pack
- Insulated Type
- SiC SBD embedded MOSFET

APPLICATION

Traction drives, High Reliability Converters / Inverters, DC choppers

OUTLINE DRAWING & CIRCUIT DIAGRAM

Dimensions in mm



CIRCUIT DIAGRAM

No.	Terminals
1, 2	DC+, D(P)
3, 4, 5	AC, S(P), D(N)
6, 7	DC-, S(N)
8	D(P)
9	G(P)
10	S(P)
11	D(N)
12	G(N)
13	S(N)
14, 15	NC

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Item	Symbol	Condition	Ratings	Unit
Drain-Source voltage, specified gate-source voltage	V_{DSX}	$V_{GS} = -7\text{ V}$ $T_J = -40 \sim 175\text{ }^{\circ}\text{C}$	3300	V
Gate-Source voltage	V_{GSS}	$V_{DS} = 0\text{ V}$ $T_J = -40 \sim 175\text{ }^{\circ}\text{C}$	± 20	V
Drain current	I_D	$V_{GS} = 17\text{ V}$, $T_c = 105\text{ }^{\circ}\text{C}$, AC terminal output current (Note 1)	200	A
Drain current	I_{DP}	Non repetitive pulse $T_J = T_{op}$	400	A
Reverse drain current (FWD forward current)	I_S	$V_{GS} = -7\text{ V}$, $T_c = 103\text{ }^{\circ}\text{C}$, AC terminal output current (Note 1)(Note 2)	200	A
Reverse drain current (FWD forward current)	I_{SP}	Non repetitive pulse (Note 2) $T_J = T_{op}$	400	A
Total power dissipation	P_{tot}	$T_c = 25\text{ }^{\circ}\text{C}$, MOSFET part (Note 3)	2080	W
Isolation voltage	V_{isol}	Charge part to the baseplate RMS sinusoidal, 60Hz 1min	6000	Vrms
Partial discharge charge	Q_{pd}	Charged part to the baseplate RMS sinusoidal, 60 Hz 1min $V_1 = 3500\text{ V}$, $V_2 = 2600\text{ V}$ (acc. to IEC 61287-1)	10	pC
Junction temperature	T_J	Maximum temperature range in off-state or on-state (non-switching)	$-40 \sim 175$	$^{\circ}\text{C}$
Case temperature	T_c	Maximum case temperature range in on-state	$-40 \sim 150$	$^{\circ}\text{C}$
Storage temperature	T_{stg}	Maximum case temperature range in off-state	$-50 \sim 175$	$^{\circ}\text{C}$
Operating junction temperature	T_{jop}	Maximum junction temperature range for switching operation	$-40 \sim 175$	$^{\circ}\text{C}$
Short-circuit withstand pulse duration	t_{psc}	$V_{DD} = 2500\text{ V}$, $V_{GS} = +17 / -7\text{ V}$, $L_s = 40\text{ nH}$, $V_{GS50\%} - V_{GS50\%}$ $T_J = T_{op}$	1.7	μs
Short circuit energy	E_{SC}	$V_{DD} = 2500\text{ V}$, $F(t)_{weibull} = 1\%$ $T_J = T_{op}$	8.7	J
Non-repetitive surge forward current	I_{FSM}	$t_p = 10\text{ms}$, $F(t)_{weibull} = 1\%$, Half sinewave $T_J = 175\text{ }^{\circ}\text{C}$	1.4	kA
I^2t value	I^2t	$t_p = 10\text{ms}$, $F(t)_{weibull} = 1\%$, Half sinewave $T_J = 175\text{ }^{\circ}\text{C}$	10	kA^2s

ELECTRICAL CHARACTERISTICS

Item	Symbol	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Gate-source leakage current	I_{GSS}	$V_{DS} = 0\text{ V}$, $V_{GS} = V_{GSS}$ $T_J = 25\text{ }^{\circ}\text{C}$	-0.5	-	0.5	μA
Drain-source cut-off current	I_{DSX}	$V_{DS} = V_{DSX}$, $V_{GS} = -7\text{ V}$ $T_J = 25\text{ }^{\circ}\text{C}$	-	0.8	-	μA
			-	12.5	-	μA
			-	20.0	750	μA
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = 10\text{ V}$, $I_D = 20\text{mA}$ $T_J = 25\text{ }^{\circ}\text{C}$	1.60	2.10	2.60	V
			-	1.50	-	V
			0.90	1.45	1.90	V
Drain-source on resistance	$r_{DS(on)}$	$V_{DS} = V_{DS(on)}$, $V_{GS} = 17\text{ V}$ $T_J = 25\text{ }^{\circ}\text{C}$	-	8.00	-	m Ω
			-	17.25	-	m Ω
			-	20.00	24.25	m Ω
Drain-source on-state voltage	$V_{DS(on)}$	$I_D = 200\text{ A}$, $V_{GS} = 17\text{ V}$ (Note 4) $T_J = 25\text{ }^{\circ}\text{C}$	-	1.60	-	V
			-	3.45	-	V
			-	4.00	4.85	V
Source-drain voltage	$V_{SD(on)}$	$I_S = 200\text{ A}$, $V_{GS} = 17\text{ V}$ (Note 4) $T_J = 25\text{ }^{\circ}\text{C}$	-	1.45	-	V
			-	3.25	-	V
			-	3.80	4.40	V
Source-drain voltage	V_{SD}	$I_S = 200\text{ A}$, $V_{GS} = 0\text{ V}$ (Note 4) $T_J = 25\text{ }^{\circ}\text{C}$	-	2.00	-	V
			-	3.85	-	V
			-	4.35	5.00	V
Source-drain voltage	$V_{SD(off)}$	$I_S = 200\text{ A}$, $V_{GS} = -7\text{ V}$ (Note 4) $T_J = 25\text{ }^{\circ}\text{C}$	-	2.00	-	V
			-	3.85	-	V
			-	4.35	5.00	V
Input capacitance	C_{iss}	$V_{DS} = 10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{kHz}$, 1/2 module $T_J = 25\text{ }^{\circ}\text{C}$	-	27.6	-	nF
Output capacitance	C_{oss}	$V_{DS} = 10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{kHz}$, 1/2 module $T_J = 25\text{ }^{\circ}\text{C}$	-	17.6	-	nF
Reverse transfer capacitance	C_{rss}	$V_{DS} = 10\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 100\text{kHz}$, 1/2 module $T_J = 25\text{ }^{\circ}\text{C}$	-	0.7	-	nF
Gate charge	Q_G	$V_{DD} = 1800\text{ V}$, $I_D = 200\text{ A}$, $V_{GS} = +17 / -7\text{ V}$, 1/2 module $T_J = 25\text{ }^{\circ}\text{C}$	-	0.8	-	μC

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Item	Symbol	Conditions		Limits			Unit
				Min.	Typ.	Max.	
Turn-on delay time	$t_{d(on)}$	$V_{DD} = 1800\text{ V}$, $I_D = 200\text{ A}$, $V_{GS} = +17\text{ V} / -7\text{ V}$, $L_s = 40\text{ nH}$	$T_J = 175\text{ }^{\circ}\text{C}$	-	-	0.37	μs
Rise time	t_r	$V_{DD} = 1800\text{ V}$, $I_D = 200\text{ A}$, $V_{GS} = +17\text{ V} / -7\text{ V}$, $L_s = 40\text{ nH}$	$T_J = 175\text{ }^{\circ}\text{C}$	-	-	0.23	μs
Turn-on (switching) energy per pulse 10% integral	$E_{on(10\%)}$	$V_{DD} = 1800\text{ V}$, $I_D = 200\text{ A}$, $V_{GS} = +17\text{ V} / -7\text{ V}$, $L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\text{ }\Omega$, $R_{G(off)} = 6.0\text{ }\Omega$, Inductive load	$T_J = 25\text{ }^{\circ}\text{C}$	-	0.07	-	J
			$T_J = 150\text{ }^{\circ}\text{C}$	-	0.06	-	J
			$T_J = 175\text{ }^{\circ}\text{C}$	-	0.06	-	J
Turn-on (switching) energy per pulse	E_{on}	$V_{DD} = 1800\text{ V}$, $I_D = 200\text{ A}$, $V_{GS} = +17\text{ V} / -7\text{ V}$, $L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\text{ }\Omega$, $R_{G(off)} = 6.0\text{ }\Omega$, Inductive load	$T_J = 25\text{ }^{\circ}\text{C}$	-	0.07	-	J
			$T_J = 150\text{ }^{\circ}\text{C}$	-	0.06	-	J
			$T_J = 175\text{ }^{\circ}\text{C}$	-	0.06	-	J
Total capacitive charge	Q_C	$V_{DD} = 1800\text{ V}$, $I_D = 200\text{ A}$, $V_{GS} = +17\text{ V} / -7\text{ V}$, $L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\text{ }\Omega$, $R_{G(off)} = 6.0\text{ }\Omega$, Inductive load	$T_J = 25\text{ }^{\circ}\text{C}$	-	2.7	-	μC
			$T_J = 150\text{ }^{\circ}\text{C}$	-	3.1	-	μC
			$T_J = 175\text{ }^{\circ}\text{C}$	-	3.1	-	μC
Diode turn-off energy (per pulse)	$E_{off_Diode(10\%)}$	$V_{DD} = 1800\text{ V}$, $I_D = 200\text{ A}$, $V_{GS} = +17\text{ V} / -7\text{ V}$, $L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\text{ }\Omega$, $R_{G(off)} = 6.0\text{ }\Omega$, Inductive load	$T_J = 25\text{ }^{\circ}\text{C}$	-	0.24	-	mJ
			$T_J = 150\text{ }^{\circ}\text{C}$	-	-	-	mJ
			$T_J = 175\text{ }^{\circ}\text{C}$	-	0.54	-	mJ
Diode switching off energy of diode	E_{off_Diode}	$V_{DD} = 1800\text{ V}$, $I_D = 200\text{ A}$, $V_{GS} = +17\text{ V} / -7\text{ V}$, $L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\text{ }\Omega$, $R_{G(off)} = 6.0\text{ }\Omega$, Inductive load	$T_J = 25\text{ }^{\circ}\text{C}$	-	0.34	-	mJ
			$T_J = 150\text{ }^{\circ}\text{C}$	-	-	-	mJ
			$T_J = 175\text{ }^{\circ}\text{C}$	-	0.65	-	mJ
Turn-off delay time	$t_{d(off)}$	$V_{DD} = 1800\text{ V}$, $I_D = 200\text{ A}$, $V_{GS} = +17\text{ V} / -7\text{ V}$, $L_s = 40\text{ nH}$	$T_J = 175\text{ }^{\circ}\text{C}$	-	-	0.94	μs
Fall time	t_f	$V_{DD} = 1800\text{ V}$, $I_D = 200\text{ A}$, $V_{GS} = +17\text{ V} / -7\text{ V}$, $L_s = 40\text{ nH}$	$T_J = 175\text{ }^{\circ}\text{C}$	-	-	0.40	μs
Turn-off (switching) energy per pulse 10% integral	$E_{off(10\%)}$	$V_{DD} = 1800\text{ V}$, $I_D = 200\text{ A}$, $V_{GS} = +17\text{ V} / -7\text{ V}$, $L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\text{ }\Omega$, $R_{G(off)} = 6.0\text{ }\Omega$, Inductive load	$T_J = 25\text{ }^{\circ}\text{C}$	-	0.03	-	J
			$T_J = 150\text{ }^{\circ}\text{C}$	-	0.03	-	J
			$T_J = 175\text{ }^{\circ}\text{C}$	-	0.03	-	J
Turn-off (switching) energy per pulse	E_{off}	$V_{DD} = 1800\text{ V}$, $I_D = 200\text{ A}$, $V_{GS} = +17\text{ V} / -7\text{ V}$, $L_s = 40\text{ nH}$ $R_{G(on)} = 1.5\text{ }\Omega$, $R_{G(off)} = 6.0\text{ }\Omega$, Inductive load	$T_J = 25\text{ }^{\circ}\text{C}$	-	0.03	-	J
			$T_J = 150\text{ }^{\circ}\text{C}$	-	0.03	-	J
			$T_J = 175\text{ }^{\circ}\text{C}$	-	0.03	-	J

THERMAL CHARACTERISTICS

Item	Symbol	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Thermal resistance junction to case	$R_{th(j-c)}$	Junction to Case, MOSFET + embeded SBD part, 1/2 module	-	-	72.0	K/kW
Contact thermal resistance case to heatsink	$R_{th(c-s)}$	Case to heat sink, $\lambda_{grease} = 1\text{ W/m}\cdot\text{K}$, $D_{(c-s)} = 70\text{ }μ\text{m}$, 1/2 module	-	57.0	-	K/kW

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Item	Symbol	Conditions	Limits			Unit
			Min.	Typ.	Max.	
Mounting torque	M _t	Main terminal screw M8 This is the case when installing the product on the bus bar	7.0	-	22.0	N·m
Mounting torque	M _t	Mounting screw M6	3.0	-	6.0	N·m
Mounting torque	M _t	Auxiliary terminals screw M3	0.4	-	0.8	N·m
mass	m	-	-	0.8	-	kg
Comparative tracking index	CTI	-	600	-	-	-
Clearance distance in air	d _a	Between main terminal	8.0	-	-	mm
Creepage distance along surface	d _s	-	32.0	-	-	mm
Internal inductance, D-S	L _{PDS}	Between DC+ and DC-(terminal1,2-6,7)	-	28	-	nH
	L _{PDS}	Between DC+ and AC, (terminal1,2-3,4,5)	-	50	-	nH
	L _{PDS}	Between AC and DC-(terminal3,4,5-6,7)	-	50	-	nH

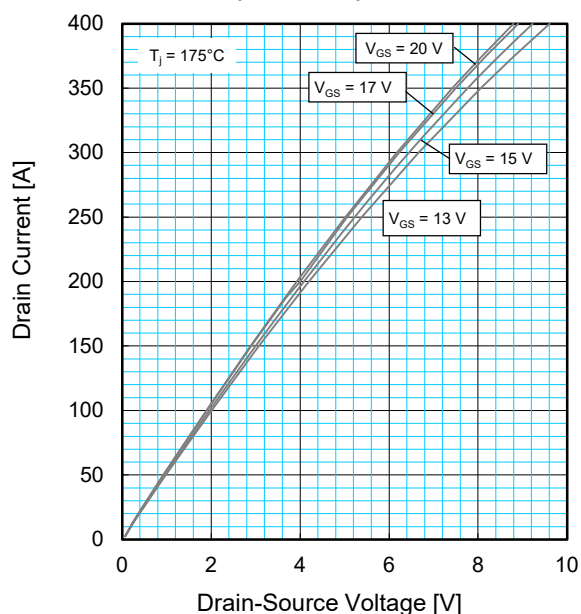
Note 1. Control Case Temperature (T_c) so that the junction temperature (T_j) does not exceed the maximum rating.

Note 2. The symbols represent characteristics of the anti-parallel, source to drain free-wheel diode (FWDi).

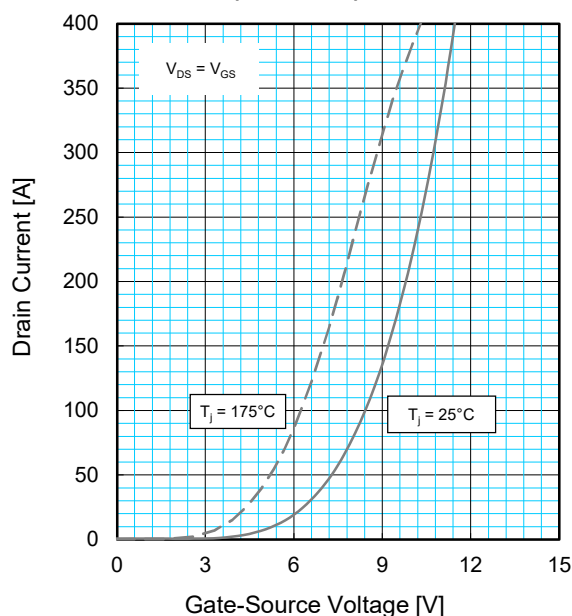
Note 3. Junction temperature (T_j) should not exceed T_{jmax} rating.

Note 4. Pulse width and repetition rate should be such as to cause negligible temperature rise.

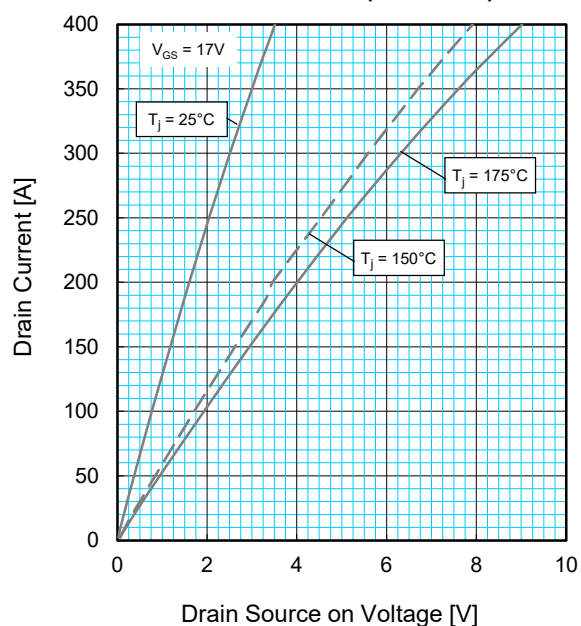
**OUTPUT CHARACTERISTICS
(TYPICAL)**



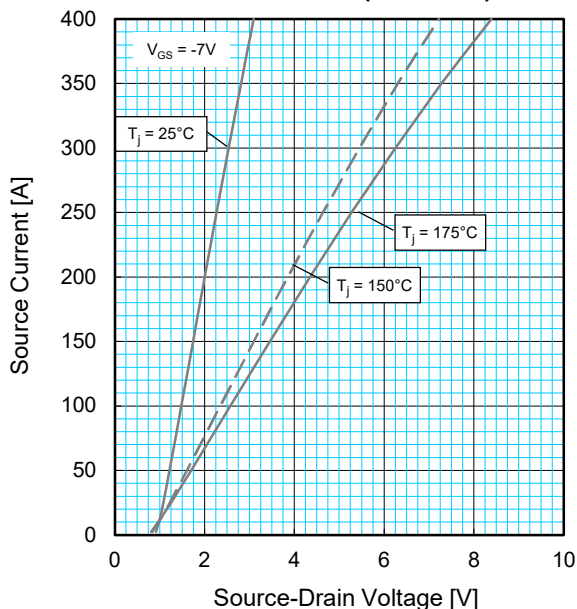
**TRANSFER CHARACTERISTICS
(TYPICAL)**



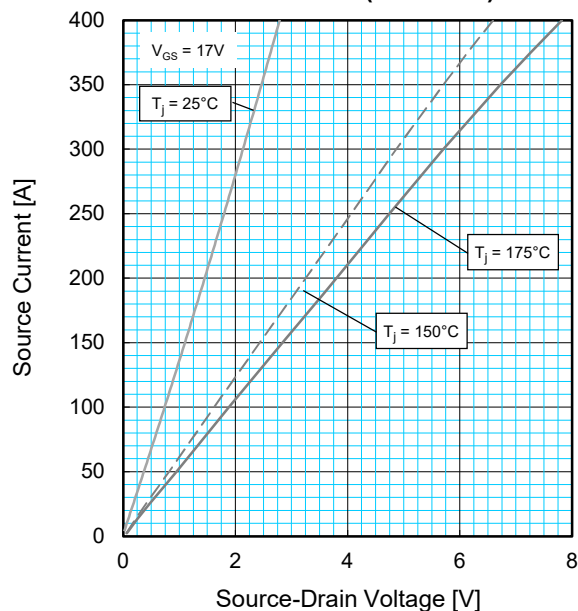
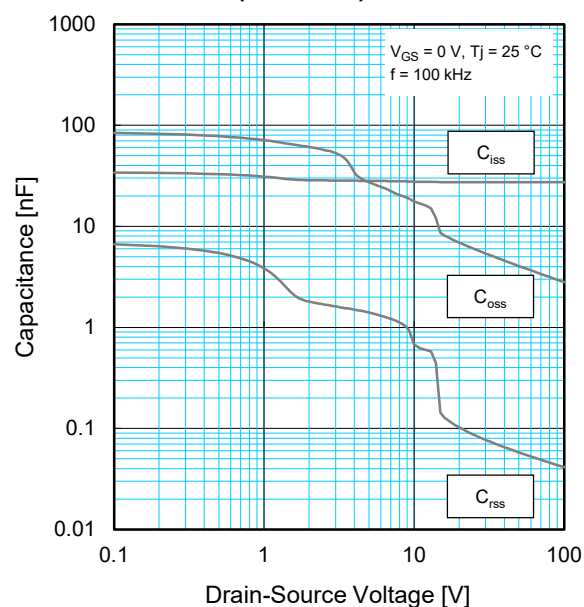
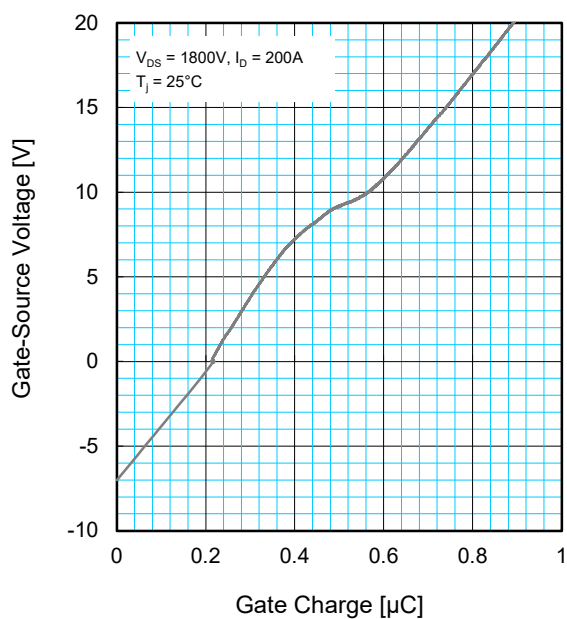
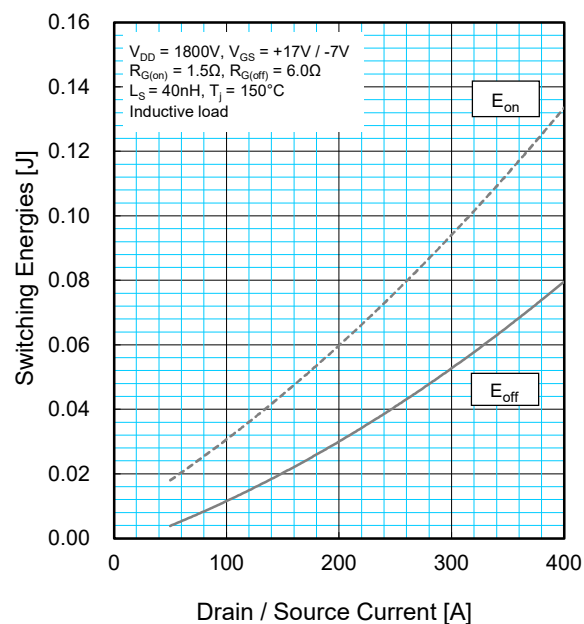
**DRAIN-SOURCE ON VOLTAGE
CHARACTERISTICS (TYPICAL)**



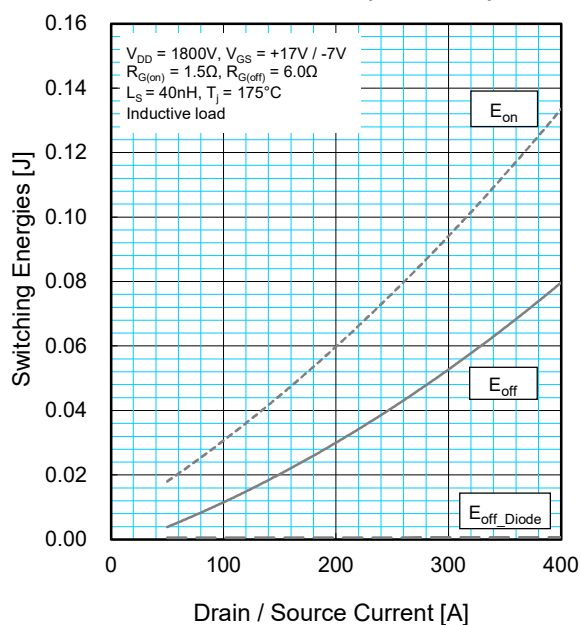
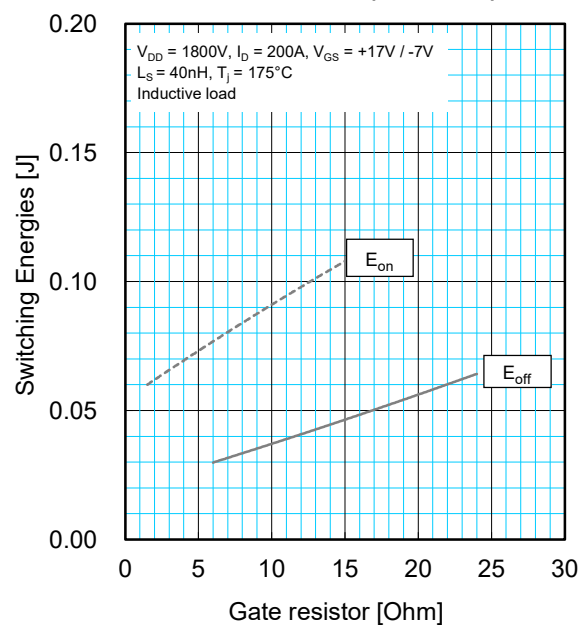
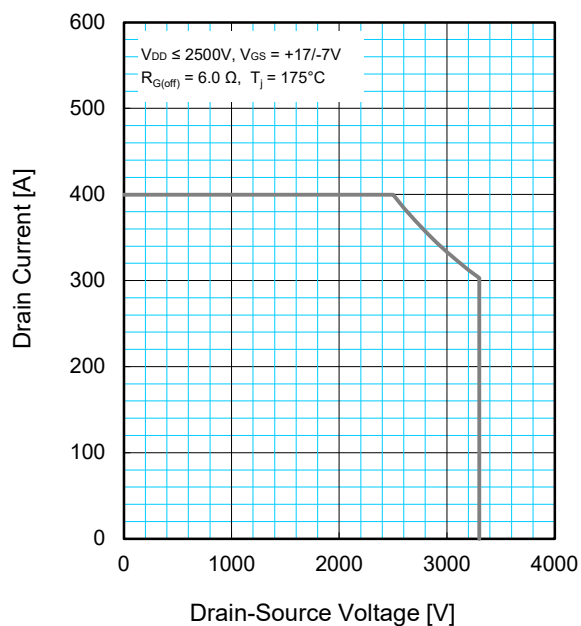
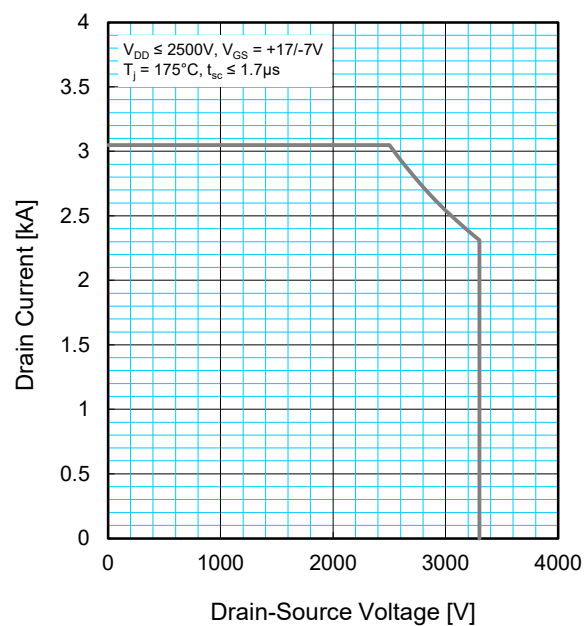
**FREE-WHEEL DIODE FORWARD
CHARACTERISTICS (TYPICAL)**



PERFORMANCE CURVES

FREE-WHEEL DIODE FORWARD CHARACTERISTICS (TYPICAL)**CAPACITANCE CHARACTERISTICS (TYPICAL)****GATE CHARGE CHARACTERISTICS (TYPICAL)****HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)**

PERFORMANCE CURVES

HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)**HALF-BRIDGE SWITCHING ENERGY CHARACTERISTICS (TYPICAL)****REVERSE BIAS SAFE OPERATING AREA (RBSOA)****SHORT CIRCUIT SAFE OPERATING AREA (SCSOA)**

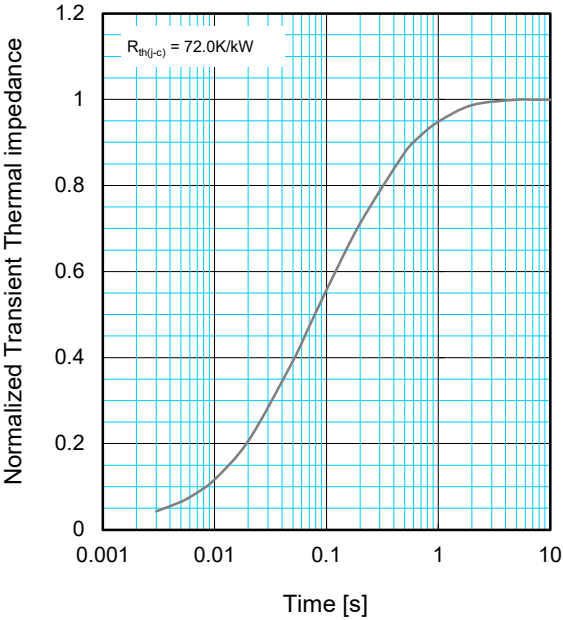
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PERFORMANCE CURVES

TRANSIENT THERMAL IMPEDANCE
CHARACTERISTICS



$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i \left\{ 1 - \exp\left(-\frac{t}{\tau_i}\right) \right\}$$

	1	2	3	4
R_i / R_{th} :	0.0078	0.1975	0.3553	0.4393
τ_i [sec.] :	0.0001	0.7324	0.0381	0.1698

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